



## APPENDIX

21. A method of making a semiconductor structure, comprising:  
plasma etching a surface of a substrate; and  
transferring heat from said substrate to (i) a seal on a support surface, and (ii) a gas in a space defined by said substrate, said seal and said support surface, substantially uniformly across said substrate, said seal being in contact with an opposing surface of said substrate.
22. The method of Claim 21, wherein said substrate is held in an assembly, said assembly comprising  
a holding body having said support surface, said holding body having an aperture for passing therethrough said gas, and  
wherein said seal has an inner peripheral portion defining an opening for receiving said gas.
23. The method of Claim 22, wherein said assembly further comprises a clamp frictionally engaging said surface of said substrate.
24. The method of Claim 21, wherein said seal has a thickness of 25 to 125 microns.
25. The method of Claim 21, wherein said seal has an outer peripheral portion with a shape substantially conforming to a shape of an outer peripheral portion of said substrate.
26. The method of Claim 22, wherein said space is substantially airtight.
27. The method of Claim 21, wherein said seal has a width of approximately 3 to 4 mm.
28. The method of Claim 21, wherein the substrate has a thickness of approximately 25 to 125 microns.

29. The method of Claim 21, wherein said gas comprises helium.
30. The method of Claim 21, wherein said seal comprises the generic material from which Kapton is made.
31. A method of making a semiconductor structure, comprising:  
a step for etching a surface of a substrate;  
wherein said substrate is in contact with means for providing substantially uniform heat transfer across said substrate.
32. The method of Claim 31, wherein said means comprises a seal, a gas and a support surface, said seal is between said substrate and said support surface, and in contact with said substrate and said support surface,  
said substrate, said seal and said support surface defining a space,  
said gas is in said space, and  
heat transfer through said seal and said first gas provides said substantially uniform heat transfer across said substrate.
33. The method of Claim 31, wherein said substrate is held in an assembly,  
said assembly comprising  
a holding body a support surface, said holding body having an aperture for passing therethrough a gas.
34. The method of Claim 32, wherein said seal has an outer peripheral portion with a shape substantially conforming to a shape of an outer peripheral portion of said substrate.
35. The method of Claim 32, wherein said space is substantially airtight.
36. The method of Claim 32, wherein said gas comprises helium.
37. A method of making a semiconductor structure, comprising:  
plasma etching a surface of a substrate;  
wherein said substrate has a substantially uniform temperature.

38. A method of making a semiconductor device, comprising:  
making a semiconductor structure by the method of Claim 21; and  
making a semiconductor device comprising the semiconductor structure.
39. A method of making an electronic device, comprising:  
making semiconductor device by the method of Claim 38; and  
making an electronic device comprising the semiconductor device.
40. In a method of making a semiconductor structure, including plasma etching a substrate, wherein the substrate is on a lower electrode, and a gas is fed through the lower electrode toward the substrate, the improvement comprising a seal between the substrate and the lower electrode having a heat conductivity providing substantially uniform heat transfer across the substrate.
41. The method of Claim 21, wherein said seal is the sole seal between said support surface and said substrate.
42. The method of Claim 31, wherein said means comprises only one seal.
43. The method of Claim 40, wherein said seal is the sole seal between said lower electrode and said substrate.